

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A semiconductor device, comprising:

a first conductive layer formed on a substrate;

an insulating interlayer positioned over the first conductive layer, the insulating interlayer having a contact hole that is at least partially disposed directly on the first conductive layer; and

a second conductive layer formed on the insulating interlayer, the second conductive layer being electrically coupled to the first conductive layer through the contact hole;

the contact hole extending beyond either an edge of the first conductive layer or an edge of the second conductive layer in plan view; and

the first conductive layer entirely overlapping the contact hole and the second conductive layer partially overlapping the contact hole in plan view.

2. (Canceled)

3. (Canceled)

4. (Currently Amended) The semiconductor device according to claim 2, claim 1, a plurality of said other conductive layers one of the first conductive layer and the second conductive layer extending parallel to one another at a predetermined pitch.

5. (Currently Amended) The semiconductor device according to claim 4, said one of the first and second conductive layers intersecting said the other of the first and second conductive layer layers.

6. (Currently Amended) The semiconductor device according to one of ~~claim 2~~,
~~said other~~claim 1, the second conductive layer overlapping the contact hole that is shifted to
one side of ~~said other~~the second conductive layer.

7. (Currently Amended) The semiconductor device according to ~~claim 2~~,~~said~~
~~other~~claim 1, the second conductive layer overlapping the contact hole, two opposing edges
of the contact hole being outside of ~~said other~~the second conductive layer.

8. (Currently Amended) The semiconductor device according to ~~claim 2~~,claim 1,
the contact hole being rectangular in plan view and the ~~other~~second conductive layer partially
overlapping the contact hole in a lengthwise direction.

9. (Currently Amended) The semiconductor device according to ~~claim 2~~,claim 1,
the contact hole being rectangular in plan view and the ~~other~~second conductive layer
extending diagonally with respect to edges of the contact hole.

10. (Original) An electro-optical unit, the semiconductor device according to
claim 1 being used for a substrate of the electro-optical unit to hold an electro-optical
substance and pixels having pixel switching transistors, and pixel electrodes being disposed
in a matrix on the substrate of the electro-optical unit.

11. (Original) The electro-optical unit according to claim 10, the electro-optical
substance being liquid crystal disposed between the substrate of the electro-optical unit and a
counter substrate.

12. (Original) The electro-optical unit according to claim 10, the electro-optical
substance being an organic electroluminescent substance that constitutes light emitting
elements on the substrate of the electro-optical unit.

13. (Original) An electronic apparatus comprising the electro-optical unit
according to claim 10.